

**Silicon PNP Power Transistors****2SA636 2SA636A****DESCRIPTION**

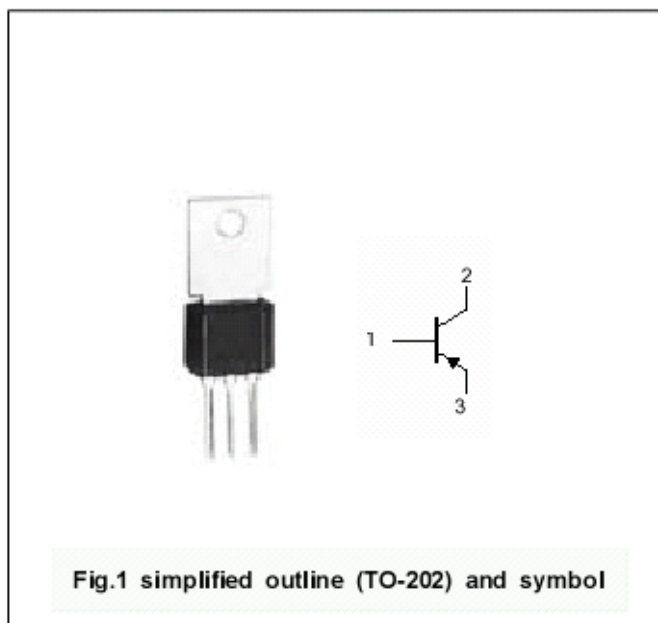
- With TO-202 package
- Complement to type 2SC1098/1098A
- High breakdown voltage
- High transition frequency

APPLICATIONS

- For audio frequency power amplifier and low speed switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Absolute maximum ratings (Ta=25℃)**

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	-70	V
V_{CEO}	Collector-emitter voltage	2SA636	Open base	-45	V
		2SA636A		-60	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-3	A
I_{CM}	Collector current-peak			-5	A
I_B	Base current			-0.6	A
P_T	Total power dissipation		$T_C=25^{\circ}\text{C}$	10	W
			$T_a=25^{\circ}\text{C}$	1.2	
T_j	Junction temperature			150	$^{\circ}\text{C}$
T_{stg}	Storage temperature			-55~150	$^{\circ}\text{C}$



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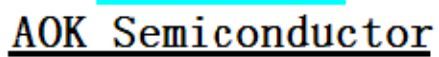
CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A ; I _B =-0.15A		-0.5	-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1.5A ; I _B =-0.15A		-0.8	-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-45V; I _E =0			-1	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-3V; I _C =0			-1	μ A
h _{FE-1}	DC current gain	I _C =-20mA ; V _{CE} =-5V	20			
h _{FE-2}	DC current gain	I _C =-0.5A ; V _{CE} =-5V	40		250	
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		60		pF
f _T	Transition frequency	I _C =-0.1A ; V _{CB} =-5V		45		MHz

◆ h_{FE-2} classifications

N	M	L	K
40-60	50-100	80-160	120-250



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PACKAGE OUTLINE

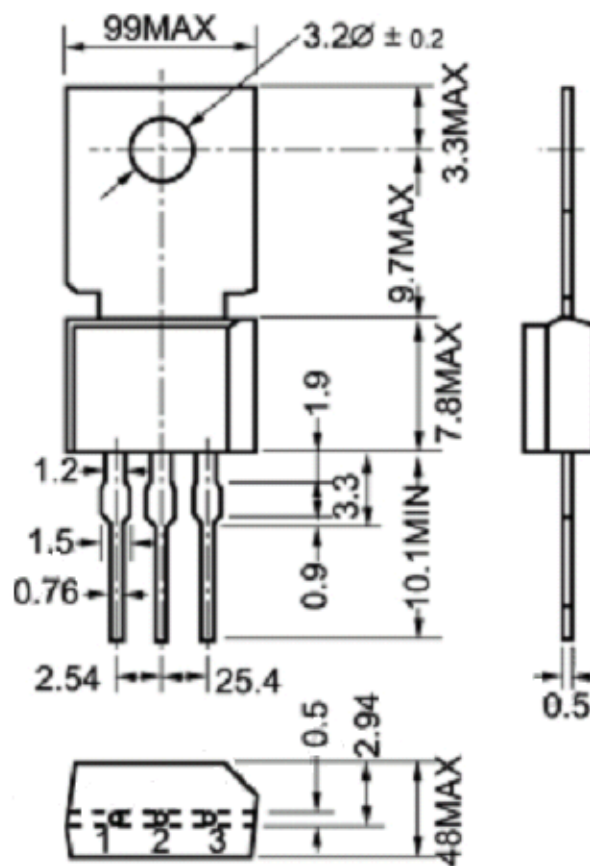


Fig.2 outline dimensions